

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11576	((427/526,527,529,539,579,533) or (438/798,766,770,771,772,787,788,453,440,439,423,407,378,297) or (205/123,157,316)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/09/12 17:20
L2	7238	(SOI GeSOI GSOI GeSiOI GESOI (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF.sub.2" boron gallium aluminum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L3	5006	(Vacancies voids pores porous porosity damag\$5 dangling adj bonds) Same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SiGe GeSi dopant doping dope\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L4	71	L2 same L3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L5	254	L2 and L3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L6	71	L4 and L5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L7	183	L5 not L6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20

L8	2317	("HF.u/c." Hydrofluoric hydrofluoride Hydrofloric hydrofloride Hydrofluoricacid hydrofluorideacid Hydro adj (fluoride fluoric floric)) Same (anodic anodization electrolytic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L9	55	L7 and L8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L10	1	L9 and L1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L11	54	L9 not L10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L12	128	L7 not (L6 or L10 or L11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L13	31	L6 and L8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L14	128	L7 not (L6 or L10 or L11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L15	56	L14 and (Vacancies voids pores porous porosity) with (percent percentages "%" grade\$2 grading different differential\$3 differentiat\$4 vary\$4 varied)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20

L16	254	(L6 or L10 or L11 or L12 or L13 or L15)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:20
L17	7	L16 and @pd>"20090312"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/12 17:22

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L18	95	((427/526,527,529,539,579,533) or (438/798,766,770,771,772,787,788,453,440,439,423,407,378,297) or (205/123,157,316)).CCLS.	UPAD	OR	OFF	2009/09/12 17:28
L19	235	(SOI GeSOI GSOI GeSiOI GESOI (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant \$7 bombard\$7 inject\$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF.sub.2" boron gallium aluminum))	UPAD	OR	ON	2009/09/12 17:29
L20	79	(Vacancies voids pores porous porosity damag\$5 dangling adj bonds) Same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SiGe GeSi dopant doping dope\$2)	UPAD	OR	ON	2009/09/12 17:30
L21	0	L19 same L20	UPAD	OR	ON	2009/09/12 17:31
L22	3	L19 and L20	UPAD	OR	ON	2009/09/12 17:31
L23	22	("HF.u/c." Hydrofluoric hydrofluoride Hydrofloric hydrofloride Hydrofluoricacid hydrofluorideacid Hydro adj (fluoride fluoric floric)) Same (anodic anodization electrolytic)	UPAD	OR	ON	2009/09/12 17:31
L24	0	L22 and L23	UPAD	OR	ON	2009/09/12 17:32
L25	0	L22 and L18	UPAD	OR	ON	2009/09/12 17:33
L26	2	L22 and (Vacancies voids pores porous porosity) with (percent percentages "%" grade\$2 grading different differential\$3 differentiat\$4 vary\$4 varied)	UPAD	OR	ON	2009/09/12 17:33
L27	6	L18 and (L19 or L20)	UPAD	OR	ON	2009/09/12 17:34
L28	3	L22 or L26	UPAD	OR	ON	2009/09/12 17:35

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